

CONDUCTIVE MEMORY STACK WITH NON-UNIFORM WIDTH

Abstract

A conductive memory stack is provided. The memory stack includes a bottom electrode, a top electrode and a multi-resistive state element that is sandwiched between the electrodes. The bottom electrode can be described as having a top face with a first surface area, the top electrode has a bottom face with a second surface area and the multi-resistive state element has a bottom face with a third surface area and a top face with a fourth surface area. The multi-resistive state element's bottom face is in contact with the bottom electrode's top face and the multi-resistive state element's top face is in contact with the top electrode's bottom face. Furthermore, the fourth surface area is not equal to the second surface area.